

#### N-CHANNEL ENHANCEMENT MODE MOSFET

#### **Product Summary**

BV <sub>DSS</sub>	R <sub>DS(ON)</sub> max	I <sub>D</sub> max T <sub>A</sub> = +25°C
	90mΩ @ V <sub>GS</sub> = 4.5V	4.2A
20V	120mΩ @ V <sub>GS</sub> = 2.5V	2.7A

# Features

- Low On-Resistance
- Low Input Capacitance
- · Fast Switching Speed
- Low Input/Output Leakage
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability
- PPAP Capable (Note 4)

#### **Description and Applications**

This MOSFET is designed to minimize the on-state resistance (R<sub>DS(on)</sub>) and yet maintain superior switching performance, making it ideal for high-efficiency power management applications.

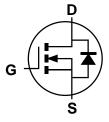
- General Purpose Interfacing Switch
- Power Management Functions
- Boost Application
- Analog Switch

#### **Mechanical Data**

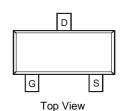
- Case: SOT23
- Case Material: Molded Plastic, "Green" Molding Compound.
   UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram
- Terminals: Finish Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 (2)
- Weight: 0.008 grams (Approximate)







Internal Schematic



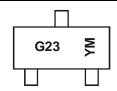
#### Ordering Information (Note 5)

Part Number	Case	Packaging
DMG2302UQ-7	SOT-23	3,000/Tape & Reel
DMG2302UQ-13	SOT-23	10,000/Tape & Reel

Notes: 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.

- 2. See http://www.diodes.com/quality/lead\_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. Automotive products are AEC-Q101 qualified and are PPAP capable. Automotive, AEC-Q101 and standard products are electrically and thermally the same, except where specified. For more information, please refer to http://www.diodes.com/quality/product\_grade\_definitions/.
- 5. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

## **Marking Information**



G23 = Product Type Marking Code YM = Date Code Marking Y = Year (ex: C = 2015) M = Month (ex: 9 = September)

Date Code Key

Year	2009	2010	2011	2012	2 201	3 20	14 2	015	2016	2017	2018	2019
Code	W	Х	Υ	Z	А		3	С	D	Е	F	G
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	N	D



### Maximum Ratings (@T<sub>A</sub> = +25°C unless otherwise specified.)

Characte	ristic		Symbol	Value	Units
Drain-Source Voltage			V <sub>DSS</sub>	20	V
Gate-Source Voltage		V <sub>GSS</sub>	±8	V	
Continuous Drain Current (Note 6)	Steady State	$T_A = +25^{\circ}C$ $T_A = +70^{\circ}C$	I <sub>D</sub>	4.2 3.4	А
Pulsed Drain Current (Note 7)		I <sub>DM</sub>	27	A	

## **Thermal Characteristics**

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 6) $T_A = +$ $T_A = +$	-25°C -70°C	0.8 0.5	w
Thermal Resistance, Junction to Ambient @T <sub>A</sub> = +25°C	$R_{\theta JA}$	156	°C/W
Operating and Storage Temperature Range	T <sub>J</sub> , T <sub>STG</sub>	-55 to +150	°C

Notes:

- 6. Device mounted on FR-4 PCB, with minimum recommended pad layout.
- 7. Repetitive rating, pulse width limited by junction temperature.

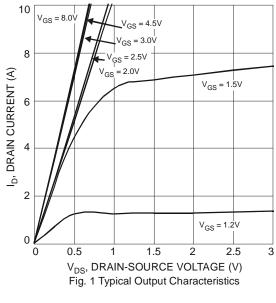
# **Electrical Characteristics** (@T<sub>A</sub> = +25°C unless otherwise specified.)

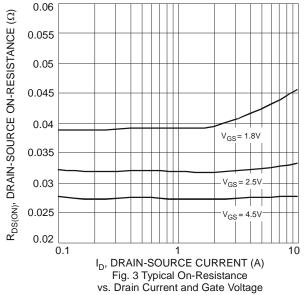
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 8)							
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	20	_	_	V	$V_{GS} = 0V, I_D = 10\mu A$	
Zero Gate Voltage Drain Current T <sub>J</sub> = +25°C	I <sub>DSS</sub>	_	_	1.0	μΑ	$V_{DS} = 20V, V_{GS} = 0V$	
Gate-Source Leakage	I <sub>GSS</sub>	-	_	±100	nA	$V_{GS} = \pm 8V$ , $V_{DS} = 0V$	
ON CHARACTERISTICS (Note 8)							
Gate Threshold Voltage	V <sub>GS(th)</sub>	0.4	_	1.0	V	$V_{DS} = V_{GS}$ , $I_D = 50\mu A$	
Static Drain-Source On-Resistance	D			90	mΩ	$V_{GS} = 4.5V, I_D = 3.6A$	
Static Dialit-Source Off-Nesistance	R <sub>DS</sub> (ON)	_	_	120	11122	$V_{GS} = 2.5V, I_D = 3.1A$	
Forward Transfer Admittance	Y <sub>fs</sub>	_	13	_	S	$V_{DS} = 5V, I_{D} = 3.6A$	
Diode Forward Voltage	$V_{SD}$	_	0.75	1.0	V	$V_{GS} = 0V, I_{S} = 1A$	
DYNAMIC CHARACTERISTICS (Note 9)							
Input Capacitance	C <sub>iss</sub>	-	594.3	_	pF	101/11/01/	
Output Capacitance	Coss	-	64.5	_	pF	$V_{DS} = 10V, V_{GS} = 0V,$ f = 1.0MHz	
Reverse Transfer Capacitance	C <sub>rss</sub>	_	57.7	_	pF	1 = 1.01/11/12	
Gate Resistance	$R_g$	_	1.5	_	Ω	$V_{DS} = 0V$ , $V_{GS} = 0V$ , $f = 1MHz$	
Total Gate Charge	Qg	_	7.0	_	nC	V 45V V 40V	
Gate-Source Charge	$Q_{gs}$	_	0.9	_	nC	$V_{GS} = 4.5V, V_{DS} = 10V,$	
Gate-Drain Charge	$Q_{gd}$	_	1.4	_	nC	$I_D = 3.6A$	
Turn-On Delay Time	t <sub>D(on)</sub>	_	7.4	_	ns		
Turn-On Rise Time	t <sub>r</sub>	-	9.8	_	ns	$V_{DD} = 10V, V_{GS} = 4.5V,$	
Turn-Off Delay Time	t <sub>D(off)</sub>	-	28.1	_	ns	$R_L = 2.78\Omega, R_G = 1.0\Omega$	
Turn-Off Fall Time	t <sub>f</sub>	_	6.7	_	ns		

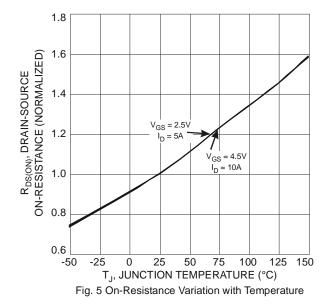
Notes:

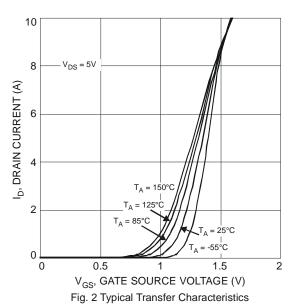
- 8. Short duration pulse test used to minimize self-heating effect. 9. Guaranteed by design. Not subject to production testing.











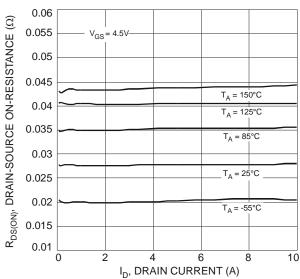


Fig. 4 Typical Drain-Source On-Resistance vs. Drain Current and Temperature

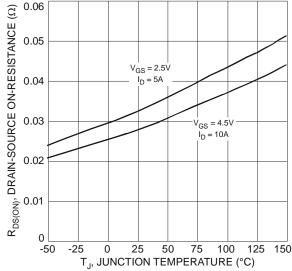


Fig. 6 On-Resistance Variation with Temperature



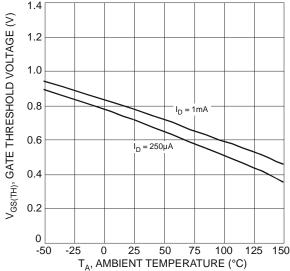
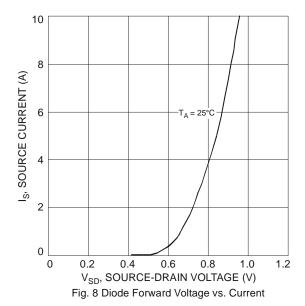
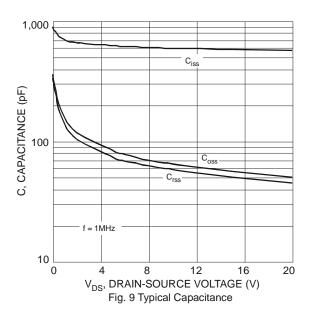


Fig. 7 Gate Threshold Variation vs. Ambient Temperature





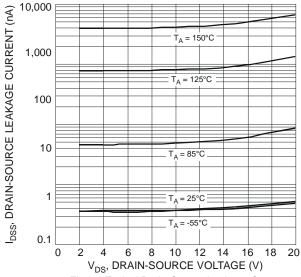


Fig. 10 Typical Drain-Source Leakage Current vs. Drain-Source Voltage

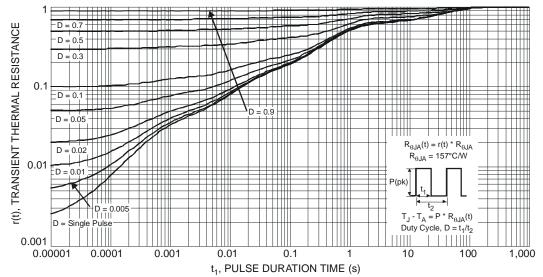
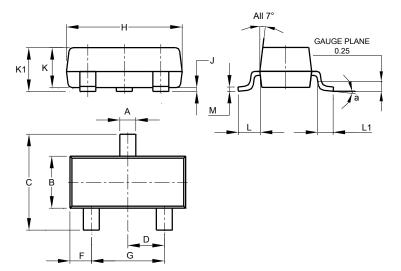


Fig. 11 Transient Thermal Response



## **Package Outline Dimensions**

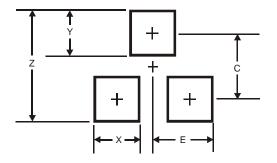
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for the latest version.



SOT23							
Dim	Min	Max	Тур				
Α	0.37	0.51	0.40				
В	1.20	1.40	1.30				
C	2.30	2.50	2.40				
D	0.89	1.03	0.915				
F	0.45	0.60	0.535				
G	1.78	2.05	1.83				
Н	2.80	3.00	2.90				
J	0.013	0.10	0.05				
K	0.890	1.00	0.975				
K1	0.903	1.10	1.025				
L	0.45	0.61	0.55				
L1	0.25	0.55	0.40				
М	0.085	0.150	0.110				
α	8°						
All Dimensions in mm							

# **Suggested Pad Layout**

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)
Z	2.9
X	0.8
Υ	0.9
С	2.0
E	1.35



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